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## Programme and Abstracts

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OXYGEN VACANCY ENHANCED GAS SENSING PERFORMANCE OF  
CeO<sub>2</sub>/GRAPHENE HETEROJUNCTION AT ROOM TEMPERATURE

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Oxygen vacancies (Ov) as the active sites have significant influences on the enhanced gas sensing performance of metal oxide. In this paper, hydrothermal process is adopted to fabricate the composites of graphene and CeO<sub>2</sub> nanoparticles, in which H<sub>2</sub>O<sub>2</sub> (L(+)-ascorbic acid (AA)) as the oxidant (reducing agent) is adopted to reduce (increase) the concentration of Ce<sup>3+</sup> ions. It is found that the sensitivity of the composites to NO<sub>2</sub> is increased gradually, as the concentration of Ce<sup>3+</sup> is increased from 14.6% to 50.7%, but decreases if the concentration of Ce<sup>3+</sup> is higher than 50.7%. First-principles calculations illustrates that CeO<sub>2</sub> becomes metallic at the Ce<sup>3+</sup> concentration of < 50.7%, the chemical potential of electrons on surface decreases and the fermi level shifts upwards, resulting in reduced Schottky barrier height (SBH) at the CeO<sub>2</sub>/Graphene interface, enhanced interfacial charge transfer and high gas sensing performance. However, deep energy level is induced at the Ce<sup>3+</sup> concentration of > 50.7%, and CeO<sub>2</sub> behaves as a semiconductor, the fermi level is pinned at the interface. As a result, the density of free electrons is reduced, leading to increased SBH and poor gas sensing response.

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